

MTG200WL60

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{RRM}	Repetitive peak reverse current	T _j =125°C, V _{RRM} applied	—	—	40	mA
I _{DRM}	Repetitive peak off-state current	T _j =125°C, V _{DRM} applied	—	—	40	mA
V _{TM}	On-state voltage	T _j =125°C, I _{TM} =600A, instantaneous meas.	—	—	1.2	V
dV/dt	Critical rate of rise of off-state voltage	T _j =125°C, V _D =2/3V _{DRM}	200	—	—	V/μs
V _{GT}	Gate trigger voltage	T _j =25°C, V _D =6V, I _G =1A	—	—	3.0	V
V _{GD}	Gate non-trigger voltage	T _j =125°C, V _D =1/2V _{DRM}	0.25	—	—	V
I _{GT}	Gate trigger current	T _j =25°C, V _D =6V, I _G =1A	15	—	150	mA
R _{th} (j-c)	Thermal resistance	Junction to case (per 1/3 module)	—	—	0.15	°C/W

Case Outline - wL-pak

